# MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

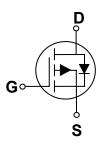
**PLED** 

# Broduct data sheet





SOT-23-3L



#### **Features**

- -20 V,-2.0A, RDS(ON) = $95m\Omega@VGS = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

#### **Applications**

- Notebook
- Load Switch
- Hand-Held Instruments

BVDSS	RDSON	ID
-20V	95mΩ	-2.0A

# **Absolute Maximum Ratings Tc=25**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
	Drain Current – Continuous (T <sub>C</sub> =250)	-2.0	Α
ID	Drain Current – Continuous (T <sub>C</sub> =1000)	-1.6	А
Ірм	Drain Current – Pulsed <sup>1</sup>	-8.0	Α
Б	Power Dissipation (T <sub>C</sub> =250)	1.56	W
P <sub>D</sub>	Power Dissipation – Derate above 250	0.012	W/ C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	С
TJ	Operating Junction Temperature Range	-55 to 150	С

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>BJA</sub> Thermal Resistance Junction to ambient			80	C/ W









#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA				V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 250 , I <sub>D</sub> =-1mA		-0.01		V/ C
	Drain-Source Leakage Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =250			-1	uA
I <sub>DSS</sub>	Drain-Gource Leakage Gurrent	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125C			-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V , V <sub>DS</sub> =0V			±100	nA

#### **On Characteristics**

Proven		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2.0A		95	120	mO.
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-1A		120	160	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	)/	-0.4	-0.7	-1.1	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA		3		mV/ C

# **Dynamic and switching Characteristics**

		-			
Qg	Total Gate Charge <sup>2, 3</sup>			3.0	
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>	$V_{DS}$ =-10V , $V_{GS}$ =-4.5V , $I_{D}$ =-1A		0.5	 nC
$Q_{gd}$	Gate-Drain Charge <sup>2, 3</sup>			8.0	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>		-	10	
Tr	Rise Time <sup>2, 3</sup>	$V_{DD}$ =-10V , $V_{GS}$ =-4.5V , $R_{G}$ =3 $\Omega$		5.5	 nS
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>	In=-1A		20	 113
Tf	Fall Time <sup>2,3</sup>			6.5	
Ciss	Input Capacitance			180	
Coss	Output Capacitance	V <sub>DS</sub> =-10V , V <sub>GS</sub> =0V , F=1MHz		35	 pF
Crss	Reverse Transfer Capacitance			25	

# **Drain-Source Diode Characteristics and Maximum Ratings**

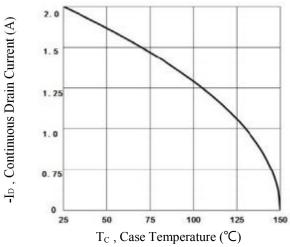
Symbol	Parameter	Conditions		Тур.	Max.	Unit
ls	Continuous Source Current	\/-=\/-=0\/ Force Current			-2.0	Α
I <sub>SM</sub>	Pulsed Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-4.0	Α
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =250			-1.2	V

#### Note:

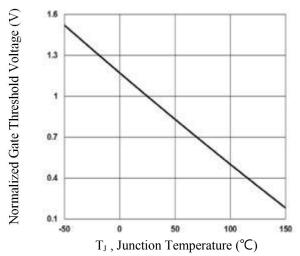
- Repetitive Rating: Pulsed width limited by maximum junction temperature.
- The data tested by pulsed , pulse width  $\leq 300 \, \text{us}$  , duty cycle  $\leq 2\%$  . 2.
- Essentially independent of operating temperature.

AO3423

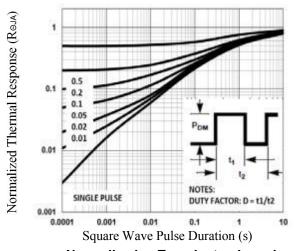




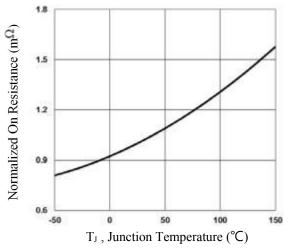
Continuous Drain Current vs. Fig. 1  $T_{c}$ 



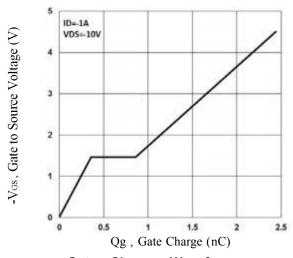
Normalized  $V_{th}$  vs.  $T_J$ 



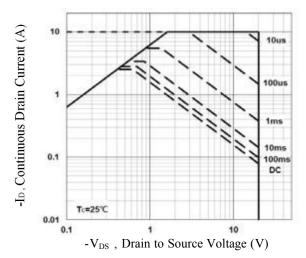
Transient Impedance Normalized



Normalized RDSON vs. T<sub>J</sub> Fig. 2

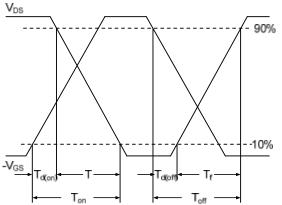


Gate Charge Waveform



Maximum Safe Operation Area Fig.6







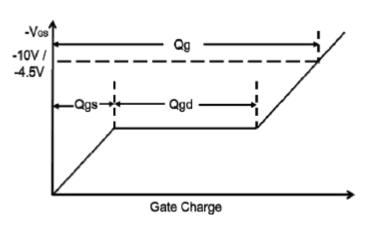
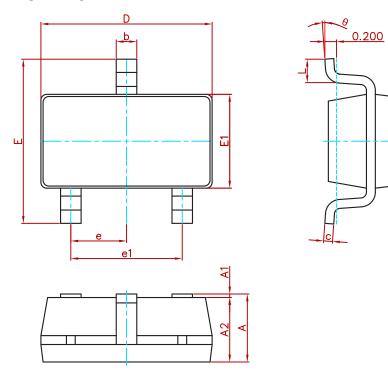


Fig. 8 Gate Charge Waveform

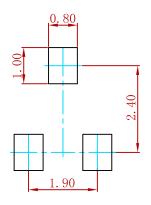


# **PACKAGE MECHANICAL DATA**



Symbol	Dimensions In	n Millimeters	Dimension	s In Inches	
Symbol	Min.	Max.	Min.	Max.	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E1	1.500	1.700	0.059	0.067	
E	2.650	2.950	0.104	0.116	
е	0.950(	BSC)	0.037(	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

# **REEL SPECIFICATION**

P/N	PKG	QTY
AO3423	SOT-23-3L	3000



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STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF PJMF280N65E1\_T0\_00201 PJMF380N65E1\_T0\_00201
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